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[Vishay/Siliconix](#)  
[IRF737LC](#)

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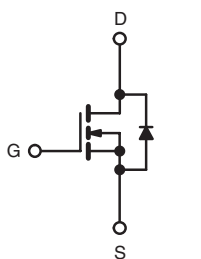
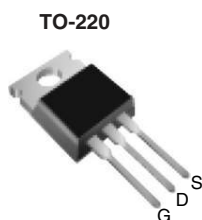


# IRF737LC, SiHF737LC

Vishay Siliconix

## Power MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	300	
R <sub>DS(on)</sub> (Ω)	V <sub>GS</sub> = 10 V	0.75
Q <sub>g</sub> (Max.) (nC)	17	
Q <sub>gs</sub> (nC)	4.8	
Q <sub>gd</sub> (nC)	7.6	
Configuration	Single	



N-Channel MOSFET

### FEATURES

- Reduced Gate Drive Requirement
- Enhanced 30 V V<sub>GS</sub> Rating
- Reduced C<sub>iss</sub>, C<sub>oss</sub>, C<sub>rss</sub>
- Extremely High Frequency Operation
- Repetitive Avalanche Rated
- Lead (Pb)-free Available



### DESCRIPTION

This new series of low charge Power MOSFETs achieve significantly lower gate charge over conventional Power MOSFETs. Utilizing the new LCDMOS technology, the device improvements are achieved without added product cost, allowing for reduced gate drive requirements and total system savings. In addition, reduced switching losses and improved efficiency are achievable in a variety of high frequency applications. Frequencies of a few MHz at high current are possible using the new low charge Power MOSFETs.

These device improvements combined with the proven ruggedness and reliability that are characteristics of Power MOSFETs offer the designer a new standard in power transistors for switching applications.

ORDERING INFORMATION	
Package	TO-220
Lead (Pb)-free	IRF737LCPbF
	SiHF737LC-E3
SnPb	IRF737LC
	SiHF737LC

ABSOLUTE MAXIMUM RATINGS T <sub>C</sub> = 25 °C, unless otherwise noted			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	300	V
Gate-Source Voltage	V <sub>GS</sub>	± 30	
Continuous Drain Current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	6.1
		T <sub>C</sub> = 100 °C	3.9
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	24	A
Linear Derating Factor		0.59	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	E <sub>AS</sub>	120	mJ
Avalanche Current <sup>a</sup>	I <sub>AR</sub>	6.1	A
Repetitive Avalanche Energy <sup>a</sup>	E <sub>AR</sub>	7.4	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	74
Peak Diode Recovery dV/dt <sup>c</sup>	dV/dt	3.4	V/ns
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s	300 <sup>d</sup>	
Mounting Torque	6-32 or M3 screw		10
			1.1

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- V<sub>DD</sub> = 25 V, starting T<sub>J</sub> = 25 °C, L = 5.7 mH, R<sub>G</sub> = 25 Ω, I<sub>AS</sub> = 6.1 A (see fig. 12).
- I<sub>SD</sub> ≤ 6.1 A, di/dt ≤ 270 A/μs, V<sub>DD</sub> ≤ V<sub>DS</sub>, T<sub>J</sub> ≤ 150 °C.
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

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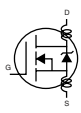

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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.7	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	300	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$	-	0.391	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 300\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	$\mu\text{A}$
		$V_{DS} = 240\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.7\text{ A}^b$	-	-	0.75	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 3.7\text{ A}^b$	2.7	-	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5	-	430	-	pF
Output Capacitance	$C_{oss}$		-	120	-	
Reverse Transfer Capacitance	$C_{rss}$		-	9.2	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}, I_D = 6.1\text{ A}, V_{DS} = 240\text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	-	17	nC
Gate-Source Charge	$Q_{gs}$		-	-	4.8	
Gate-Drain Charge	$Q_{gd}$		-	-	7.6	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 150\text{ V}, I_D = 6.1\text{ A}, R_G = 12\text{ }\Omega, R_D = 24\text{ }\Omega$ , see fig. 10 <sup>b</sup>	-	6.6	-	ns
Rise Time	$t_r$		-	21	-	
Turn-Off Delay Time	$t_{d(off)}$		-	13	-	
Fall Time	$t_f$		-	12	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	$L_S$		-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	6.1	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	24	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 6.1\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.6	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 6.1\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	320	490	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	1.5	2.2	$\mu\text{C}$

**Notes**

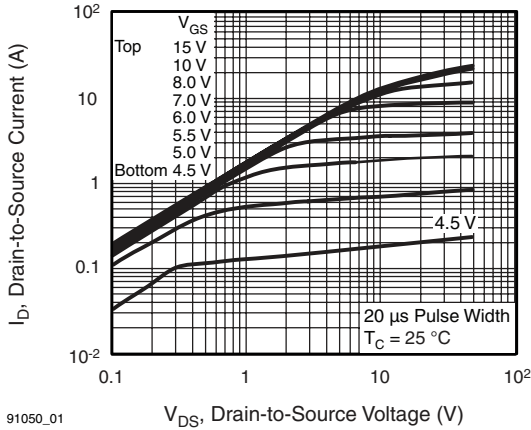
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .



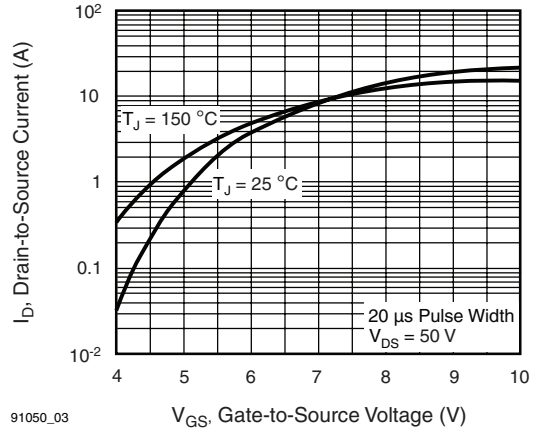
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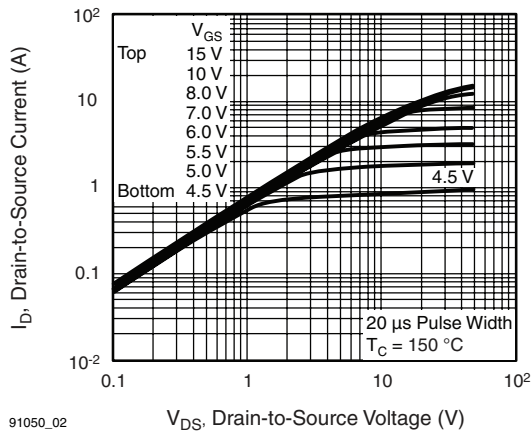
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



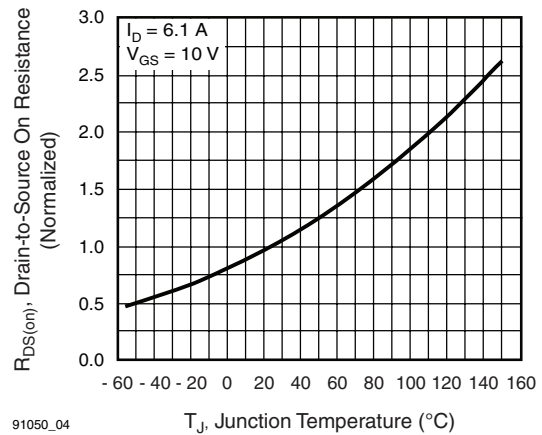
**Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$**



**Fig. 3 - Typical Transfer Characteristics**



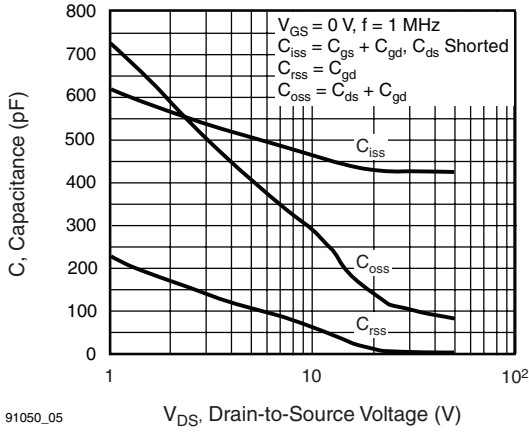
**Fig. 2 - Typical Output Characteristics,  $T_C = 150^\circ\text{C}$**



**Fig. 4 - Normalized On-Resistance vs. Temperature**

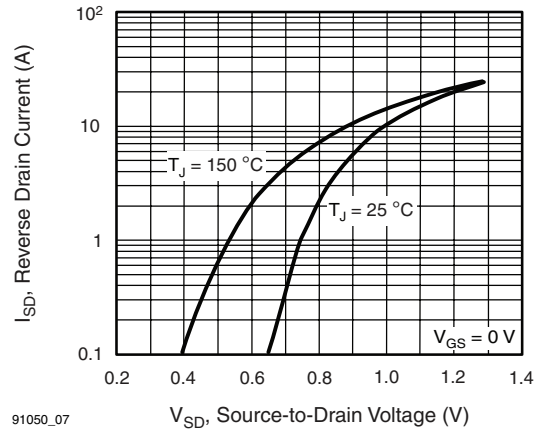
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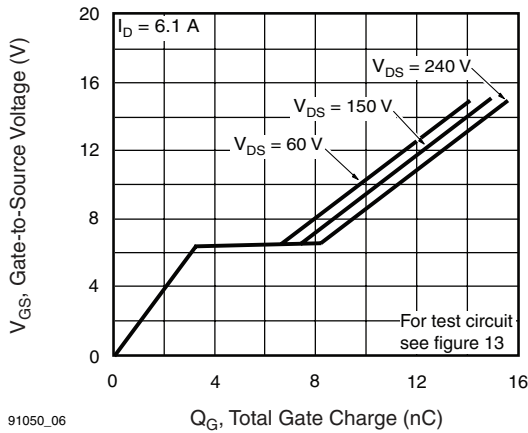
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**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



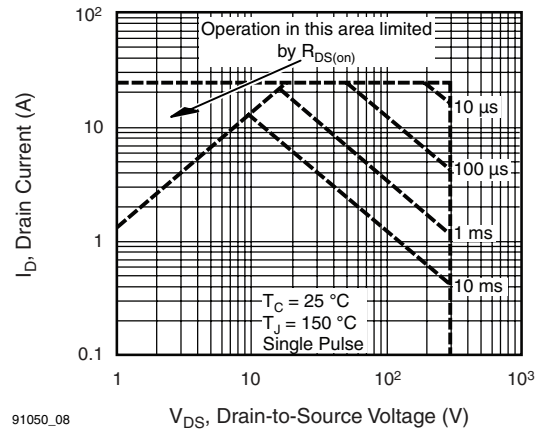
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**Fig. 7 - Typical Source-Drain Diode Forward Voltage**



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**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**

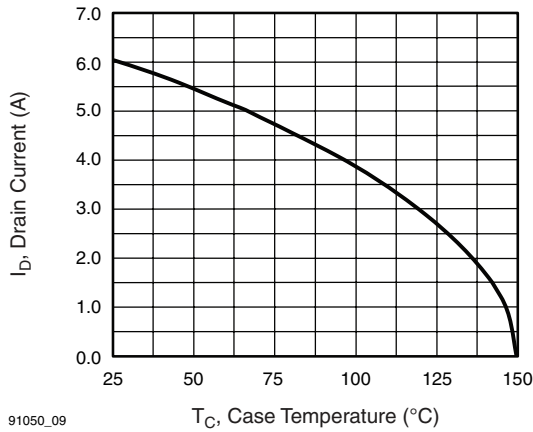


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**Fig. 8 - Maximum Safe Operating Area**

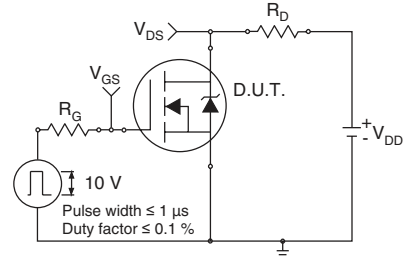


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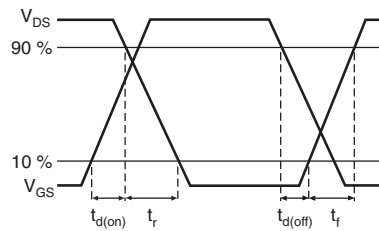


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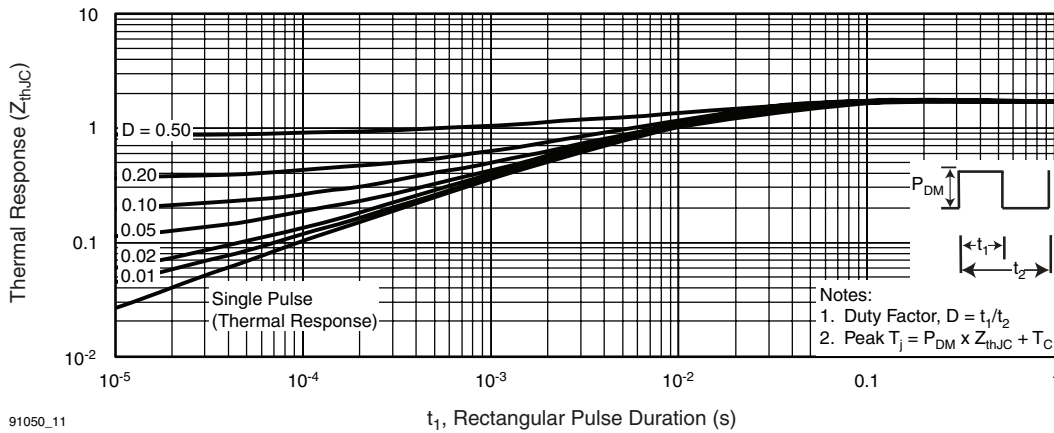
**Fig. 9 - Maximum Drain Current vs. Case Temperature**



**Fig. 10a - Switching Time Test Circuit**

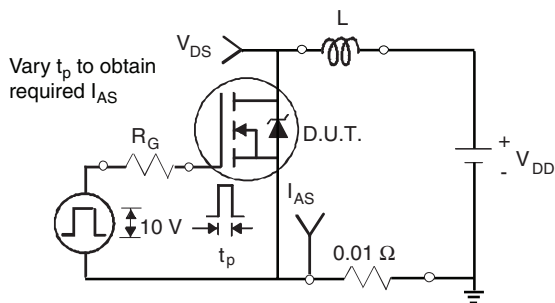


**Fig. 10b - Switching Time Waveforms**

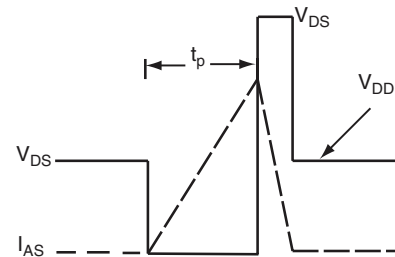


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**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



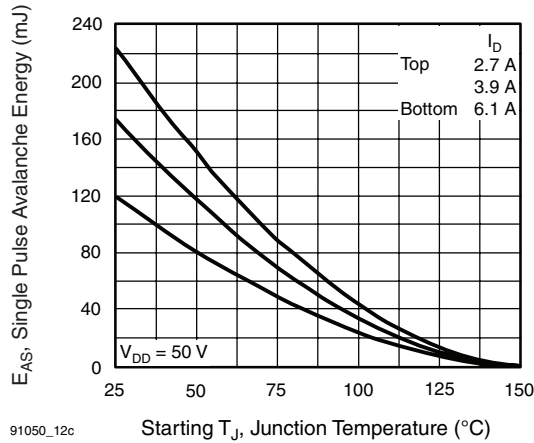
**Fig. 12a - Unclamped Inductive Test Circuit**



**Fig. 12b - Unclamped Inductive Waveforms**

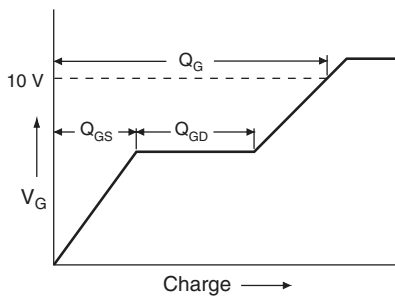
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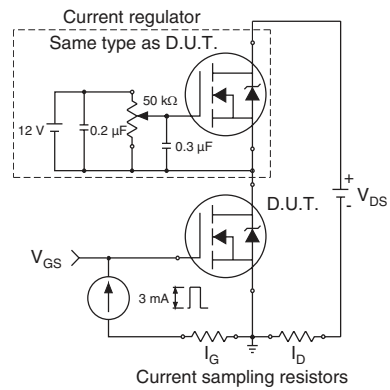


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**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**



**Fig. 13a - Basic Gate Charge Waveform**



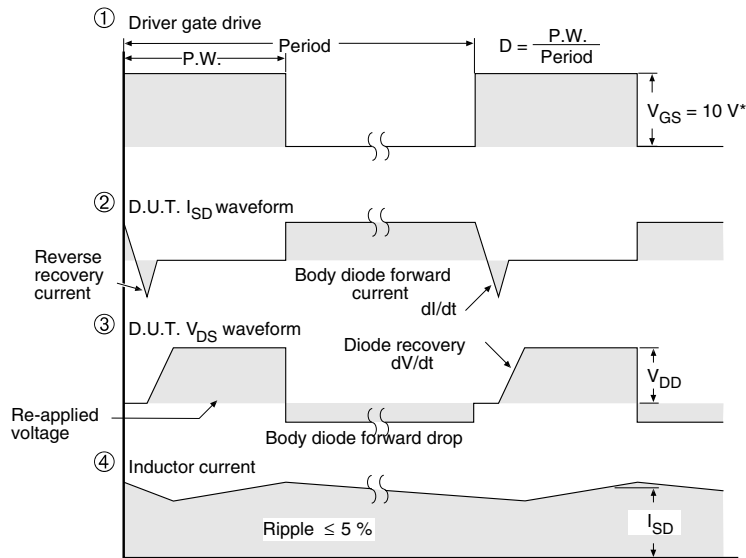
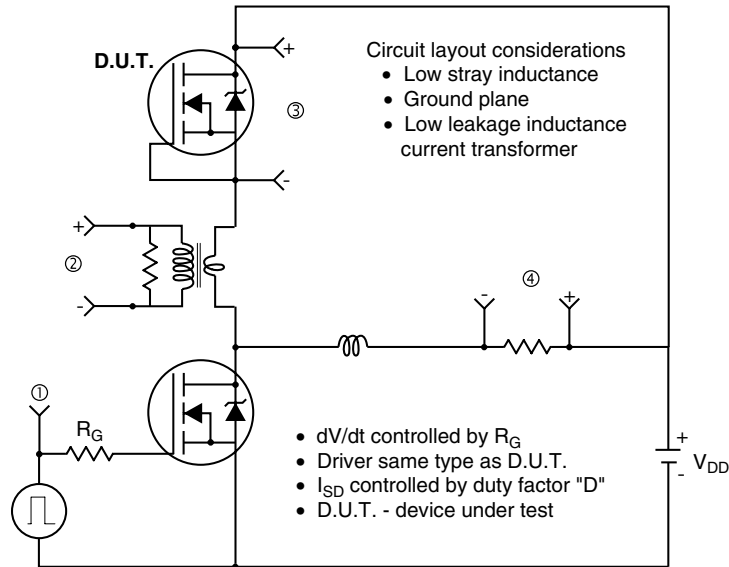
**Fig. 13b - Gate Charge Test Circuit**



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**Peak Diode Recovery dV/dt Test Circuit**



\*  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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